NDUL03N150C

N-Channel Power MOSFET 1500V, 2.5A, 10.5Ω, TO-3PF-3L



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TO-3PF-3L

Features

- ON-resistance RDS(on)=8 Ω (typ.)
- Input capacitance Ciss=650pF (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		1500	V
Gate to Source Voltage	V _{GSS}		±30	V
Drain Current (DC)	ID	Limited only maximum temperature Tch=150°C	2.5	А
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	5	А
Allowable Power Dissipation	Do		3.0	W
	PD	Tc=25°C	50	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *1	EAS		34	mJ
Avalanche Current *2	IAV		2.5	А

Note :*1 V_{DD} =50V, L=10mH, I_{AV} =2.5A (Fig.1)

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

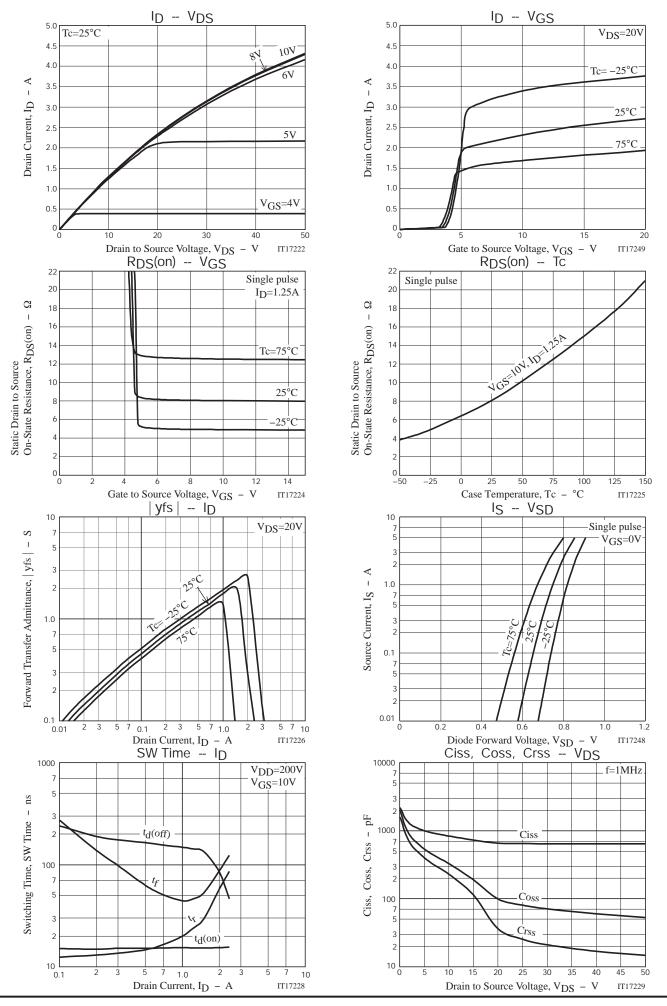
Electrical Characteristics at Ta=25°C

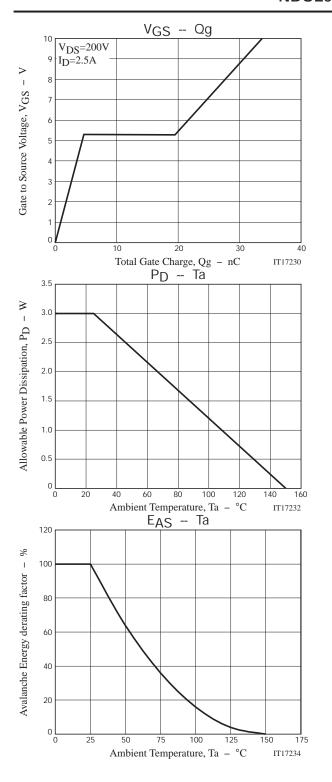
Parameter	Symbol	Conditions	Ratings			11.0
			min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	1500			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =1200V, V _{GS} =0V			1	mA
Gate to Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	2		4	V
Forward Transfer Admittance	yfs	V _{DS} =20V, I _D =1.25A		1.9		S
Static Drain to Source On-State Resistance	RDS(on)	ID=1.25A, VGS=10V		8	10.5	Ω
Input Capacitance	Ciss			650		pF
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		70		pF
Reverse Transfer Capacitance	Crss			20		pF
Turn-ON Delay Time	t _d (on)	See Fig.2		15		ns
Rise Time	t _r			24		ns
Turn-OFF Delay Time	t _d (off)			140		ns
Fall Time	tf			47		ns
Total Gate Charge	Qg	V _{DS} =200V, V _{GS} =10V, I _D =2.5A		34		nC
Gate to Source Charge	Qgs			4.7		nC
Gate to Drain "Miller" Charge	Qgd			15		nC
Diode Forward Voltage	V _{SD}	I _S =2.5A, V _{GS} =0V		0.8	1.5	V
Reverse Recovery Time	t _{rr}	See Fig.3		350		ns
Reverse Recovery Charge	Q _{rr}	I _S =2.5A, V _{GS} =0V, di/dt=100A/μs		2220		nC

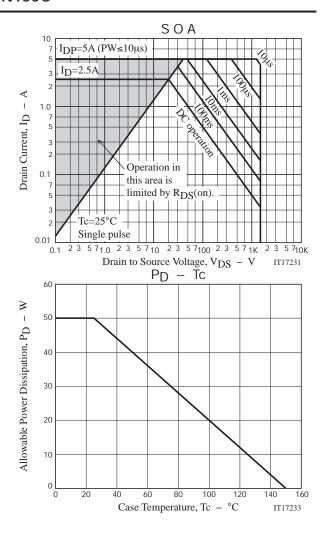
ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

^{*2} L≤10mH, single pulse







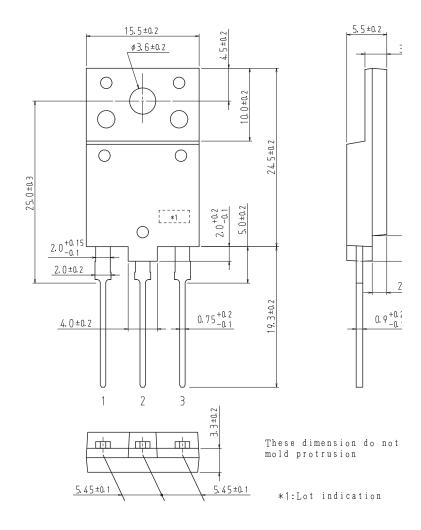
Package Dimensions NDUL03N150CG

TO-3PF-3L CASE 340AH ISSUE O Unit: mm

1: Gate

2: Drain

3: Source



Ordering & Package Information

Device	Package	Shipping	memo
NDUL03N150CG	TO-3PF-3L SC-94	30 pcs./tube	Pb-Free

Marking

Electrical Connection



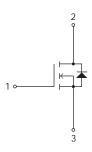
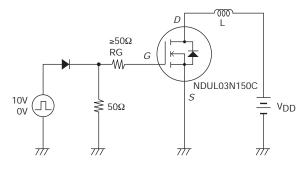


Fig.1 Unclamped Inductive Switching Test Circuit

Fig.2 Switching Time Test Circuit



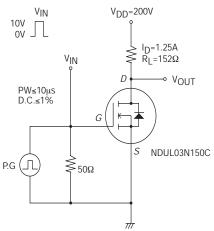
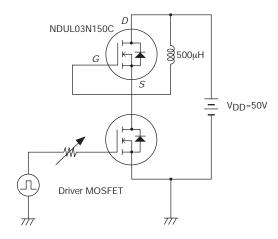


Fig.3 Reverse Recovery Time Test Circuit



Note on usage: Since the NDUL03N150C is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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